

(Withdrawn) 1. A method for preparing a photoresist layer for e-beam inspection comprising:

5 out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

(Withdrawn) 2. The method for of claim 1 wherein:

10 said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

15 (Withdrawn) 3. A method for preparing a photoresist layer for e-beam inspection comprising:

increasing a conductivity of said photoresist layer whereby electric charging of said photoresist layer during said e-beam inspection is substantially prevented.

20 (Withdrawn) 4. The method for of claim 3 wherein:

25 said step of increasing a conductivity of said photoresist layer further comprising a step of implanting conductive ions into said photoresist layer to increase a conductivity of said photoresist layer.

(Withdrawn) 5. The method for of claim 3 wherein:

30 said step of increasing a conductivity of said photoresist layer further comprising a step of implanting carbon ions into said photoresist layer.

(Withdrawn) 6. The method for of claim 3 wherein:

5                    said step of increasing a conductivity of said photoresist layer further comprising a step of implanting indium ions into said photoresist layer.

(Withdrawn) 7. The method for of claim 3 wherein:

10                  said step of increasing a conductivity of said photoresist layer further comprising a step of implanting Sb ions into said photoresist layer.

(Withdrawn) 8. The method for of claim 3 wherein:

15                  said step of increasing a conductivity of said photoresist layer further comprising a step of implanting silicon ions into said photoresist layer.

(Withdrawn) 9. The method for of claim 3 wherein:

20                  said step of increasing a conductivity of said photoresist layer further comprising a step of implanting metallic ions into said photoresist layer.

25                  (Withdrawn) 10. The method for of claim 3 wherein:

30                  said step of increasing a conductivity of said photoresist layer further comprising a step of implanting a conductive ions at an implanting energy approximately 1000 ev into said photoresist layer.

(Withdrawn) 11. The method for of claim 3 wherein:

5                   said step of increasing a conductivity of said photoresist layer further comprising a step of implanting a conductive ions having an ion dosage in a approximate range  $10^{16} / \text{cm}^2$  to  $10^{18} / \text{cm}^2$  into said photoresist layer.

(Withdrawn) 12. The method for of claim 3 wherein:

10                  said step of increasing a conductivity of said photoresist layer further comprising a step of plasma immersing ion implant a conductive ions into said photoresist layer.

(Withdrawn) 13. The method for of claim 3 further comprising:

15                  out-gassing said photoresist layer whereby an outgas from said photoresist layer during said e-beam inspection is substantially prevented.

20                  (Withdrawn) 14. The method for of claim 13 wherein:

                        said step of out-gassing said photoresist layer further comprising a step of implanting ions into said photoresist layer to activate an out-gassing from said photoresist layer.

25                  (Original ) 15. A photoresist layer for integrated circuit manufacture processed for e-beam inspection comprising:

30                  an out-gas content less than 0.5 percents thus substantially prevent out-gassing from said photoresist layer during said e-beam inspection.

(Original ) 16. A photoresist layer for integrated circuit manufacture processed for e-beam inspection comprising:

5 an electric resistivity less than 2000 ohm/cm<sup>2</sup> thus substantially prevent an electric charging of said photoresist layer during said e-beam inspection.

(Original ) 17. A photoresist layer for integrated circuit manufacture comprising:

10 implanted conductive ions for increasing a conductivity of said photoresist layer.

(Original ) 18. The photoresist layer for of claim 17 wherein:

15 said implanted conductive ions further comprising implanted carbon ions.

(Original ) 19. The photoresist layer for of claim 17 wherein:

20 said implanted conductive ions further comprising implanted indium ions.

(Original ) 20. The photoresist layer for of claim 17 wherein:

25 said implanted conductive ions further comprising implanted Sb ions.

(Original ) 21. The photoresist layer for of claim 17 wherein:

30 said implanted conductive ions further comprising implanted silicon ions.

(Original ) 22. The photoresist layer for of claim 17 wherein:

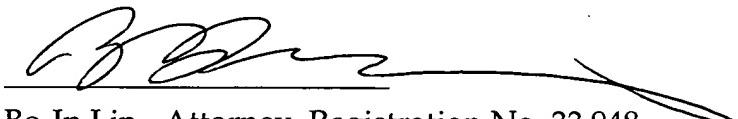
said implanted conductive ions further comprising  
implanted metallic ions.

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Respectfully submitted  
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